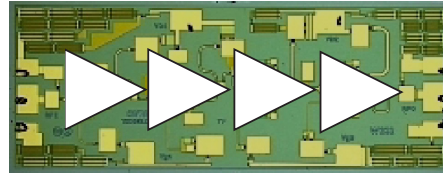


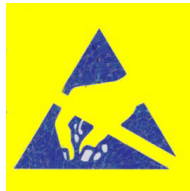
Data Sheet



Chip Size: 800 μm x 2000 μm (31.5 x 78.74 mils)
Chip Size Tolerance: ± 10 μm (± 0.4 mils)
Chip Thickness: 100 ± 10 μm (4 ± 0.4 mils)
Pad Dimensions: 100 x 100 μm (4 x 4 mils)

Description

Avago Technologies AMMC-6232 is an easy-to-use broadband, high gain, high linearity Low Noise Amplifier that operates from 18 GHz to 32GHz. The wide band and unconditionally stable performance makes this MMIC ideal as a primary or sub-sequential low noise block or a transmitter or LO driver. The MMIC has 4 gain stages and requires a 4V, 135mA power supply for optimal performance. The two gate bias voltages can be combined for ease of use or separated for more control flexibility. DC-block capacitors are integrated at the input and output stages. Since this MMIC covers several bands, it can reduce part inventory and increase volume purchase options. The MMIC is fabricated using PHEMT technology to provide exceptional low noise, gain and power performance. The backside of the chip is both RF and DC ground which helps simplify the assembly process and reduce assembly related performance variations and cost.



Attention: Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model (Class A)
ESD Human Body Model (Class 1A)
Refer to Avago Application Note A004R:
Electrostatic Discharge Damage and Control

Features

- 800 μm x 2000 μm Die Size
- Unconditionally Stable

Specifications (Vdd = 4.0V, Idd = 135mA)

- RF Frequencies: 18 - 32 GHz
- High Output IP3: 29dBm
- High Small-Signal Gain: 27dB
- Typical Noise Figure: 2.8dB
- Input, Output Match: -10dB

Applications

- Microwave Radio systems
- Satellite VSAT, DBS Up/Down Link
- LMDS & Pt-Pt mmW Long Haul
- Broadband Wireless Access (including 802.16 and 802.20 WiMax)
- WLL and MMDS loops

Note:

1. This MMIC uses depletion mode pHEMT devices.

Absolute Maximum Ratings ^[1]

Parameters / Conditions	Symbol	Unit	Max
Drain to Ground Voltage	Vdd	V	5.5
Gate-Drain Voltage	Vgd	V	-8
Drain Current	Idd	mA	200
Gate Bias Voltage	Vg	V	+0.8
Gate Bias Current	Ig	mA	1
RF CW Input Power Max	Pin	dBm	15
Max channel temperature	Tch	C	+150
Storage temperature	stg	C	-65 +150
Maximum Assembly Temp	Tmax	C	260 for 20s

Notes

1. Operation in excess of any of these conditions may result in permanent damage to this device. The absolute maximum ratings for Vdd, Vgd, Idd, Vg, Ig and Pin were determined at an ambient temperature of 25°C unless noted otherwise.

DC Specifications/ Physical Properties ^[2]

Parameter and Test Condition	Symbol	Unit	Min	Typ	Max
Drain Supply Current (Vd=4.0 V)	Idd	mA		135	150
Drain Supply Voltage	Vd	V	3	4	5
Gate Bias Current	Ig	mA		0.1	
Gate Bias Voltage	Vg	V	-1.3	-0.95	-0.55
Thermal Resistance(3)	θ_{jc}	°C/W		35.1	

2. Ambient operational temperature TA=25°C unless noted

3. Channel-to-backside Thermal Resistance (Tchannel = 34°C) as measured using infrared microscopy. Thermal Resistance at backside temp. (Tb) = 25°C calculated from measured data.

AMMC-6232 RF Specifications ^[4]

TA= 25°C, Vdd = 4.0 V, Idd = 135mA, Zo=50 Ω

Parameters and Test Conditions	Symbol	Unit	Frequency (GHz)	Spec		
				Min	Typ	Max
Small signal gain ⁽⁴⁾	AGain	dB	20	23	32	
			26	23	26.7	
			31	23	24.6	
Noise Figure into 50Ω ⁽⁴⁾	NF	dB	20		3.2	4.5
			26		3.3	4.5
			31		4	4.5
Output Power at 1dB Gain Compression ⁽⁴⁾	P1dB	dBm	20, 26, 31	15	20	
Output Third Order Intercept Point ⁽⁴⁾	OIP3	dBm	20	26	28	
			26	26	28	
			31	26	27	
Isolation	S12	dB	20, 26, 31		-50	
Input Return Loss	S11	dB	20, 26, 31		-10	
Output Return Loss	S22	dB	20, 26, 31		-10	

4. All tested parameters guaranteed with measurement accuracy ±5dBm for OPI3 and ± 2dB for gain, NF and P1dB.

AMMC-6232 Typical Performance[1]

($T_A = 25^\circ\text{C}$, $V_{dd}=4\text{V}$, $I_{dd}=135\text{mA}$, $Z_{in} = Z_{out} = 50 \Omega$, on-wafer unless noted)

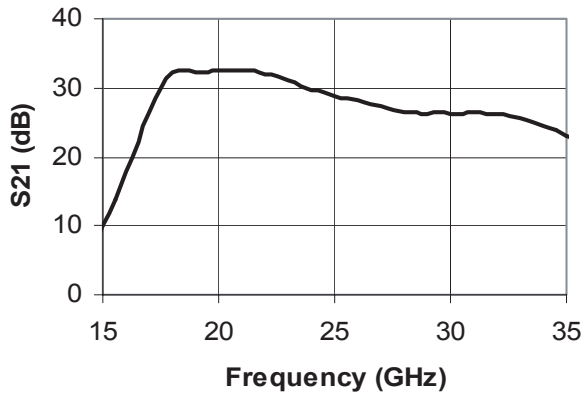


Figure 1. Small-signal Gain

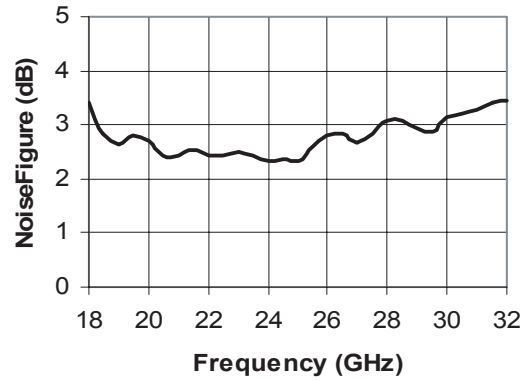


Figure 2. Noise Figure

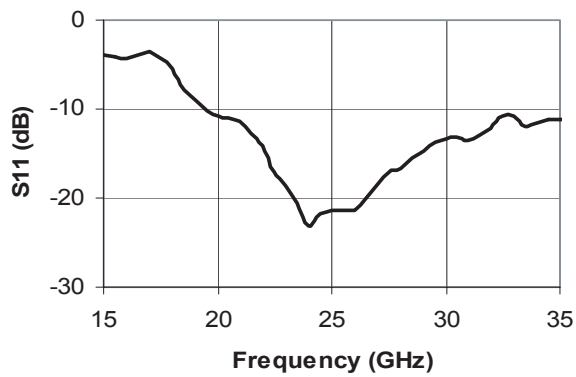


Figure 3. Input Return Loss

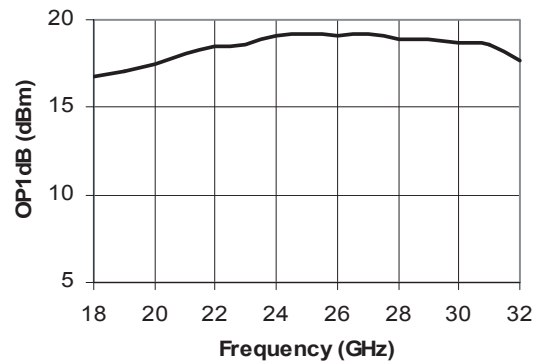


Figure 4. Output P-1dB

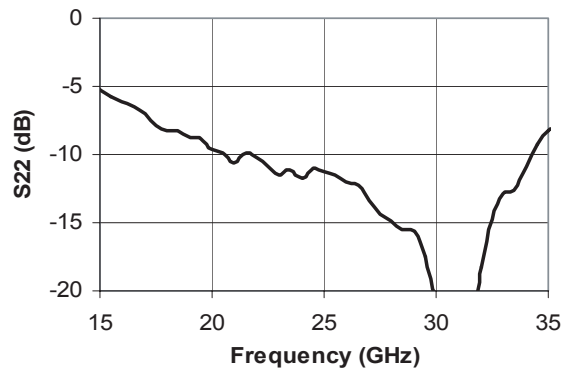


Figure 5. Output Return Loss

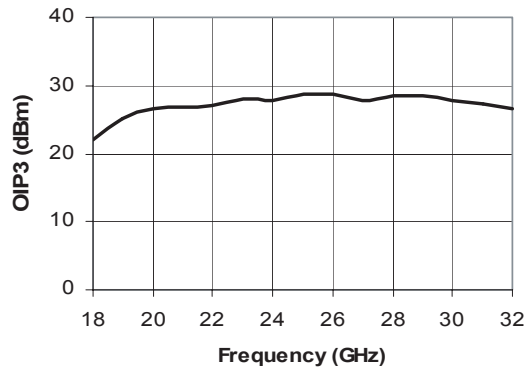


Figure 6. Output IP3

Note

1. Noise Figure is measured with a 3-dB pad at the input .

AMMC-6232 Typical Performance (Cont)

($T_A = 25^\circ\text{C}$, $V_{dd}=4\text{V}$, $I_{dd}=135\text{mA}$, $Z_{in} = Z_{out} = 50 \Omega$, on-wafer unless noted)

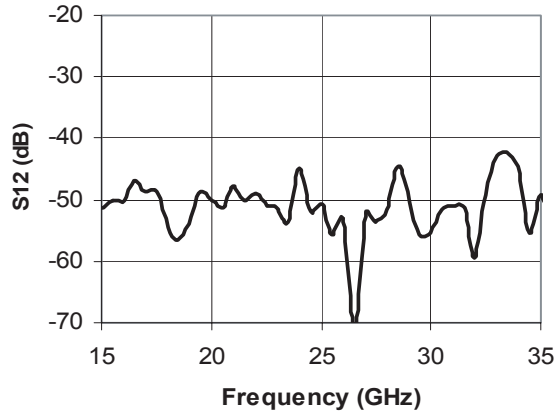


Figure 7. Isolation

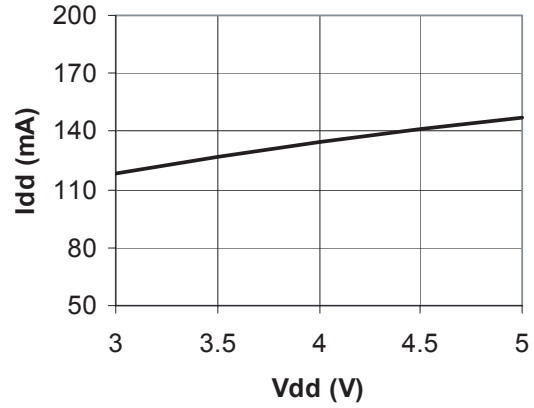


Figure 8. I_{dd} Over V_{dd} (same V_g)

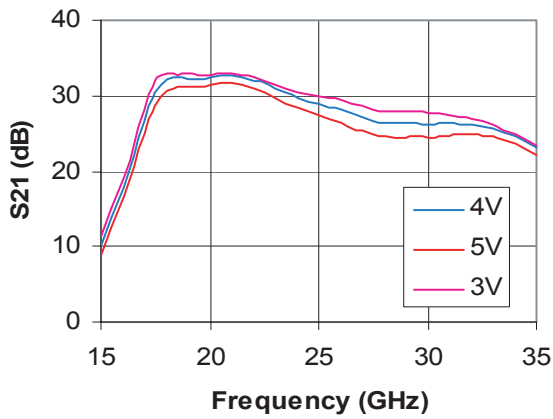


Figure 9. Small-signal Gain Over V_{dd}

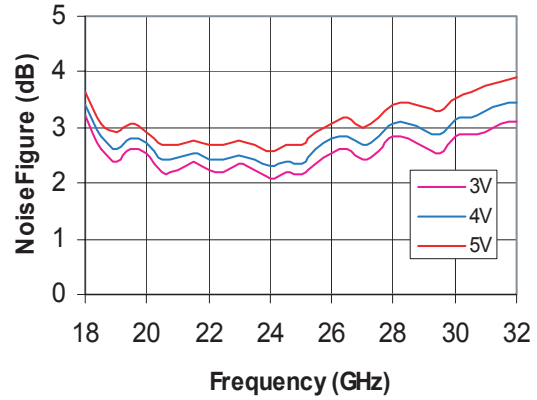


Figure 10. Noise Figure Over V_{dd}

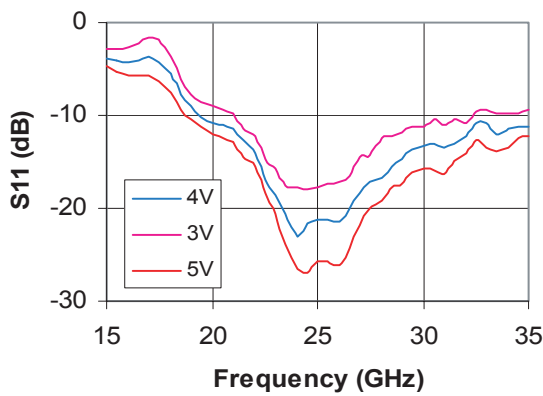


Figure 11. Input Return Loss Over V_{dd}

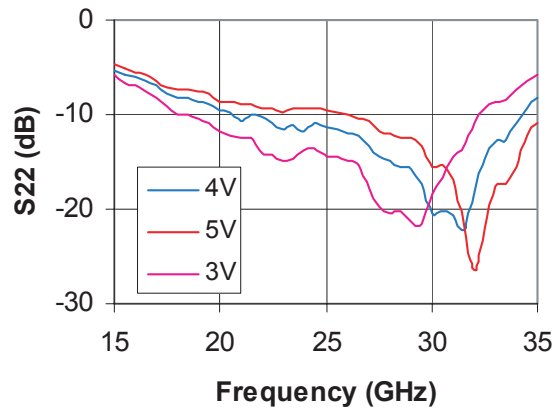


Figure 12. Output Return Loss Over V_{dd}

AMMC-6232 Typical Performance (Cont)

($T_A = 25^\circ\text{C}$, $V_{dd}=4\text{V}$, $I_{dd}=135\text{mA}$, $Z_{in} = Z_{out} = 50 \Omega$, on-wafer unless noted)

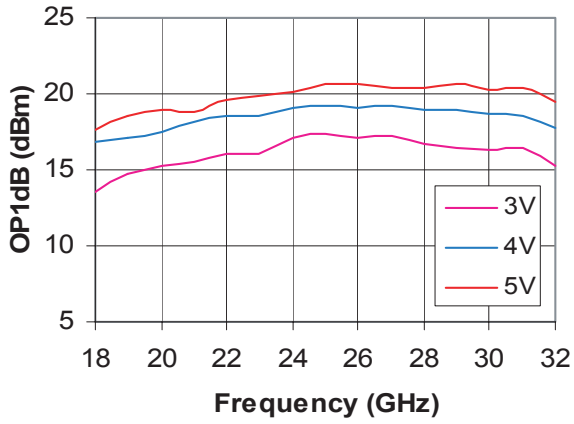


Figure 13. Output P1dB Over Vdd

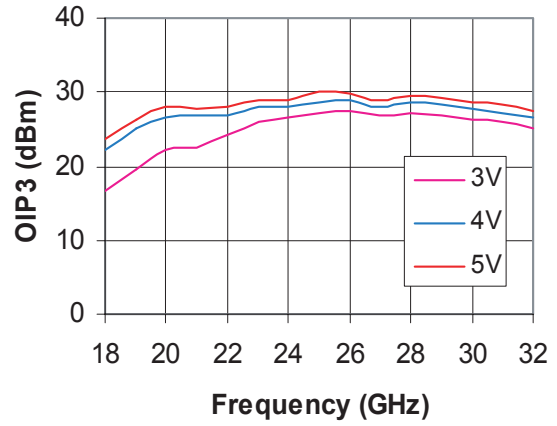


Figure 14. Output IP3 Over Vdd

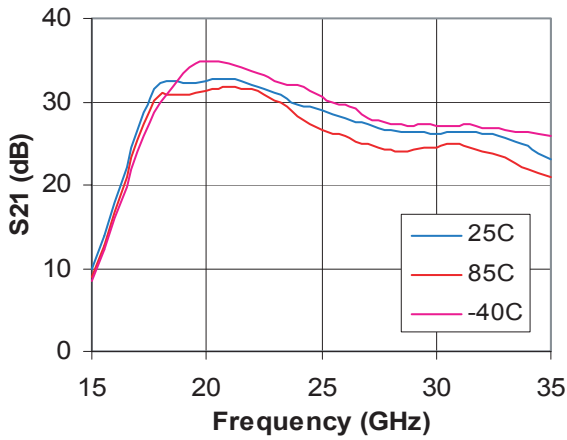


Figure 15. Small-signal Gain Over Temperature

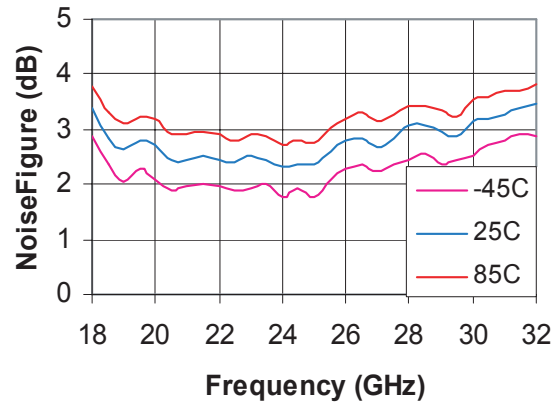


Figure 16. Noise Figure Over Temperature

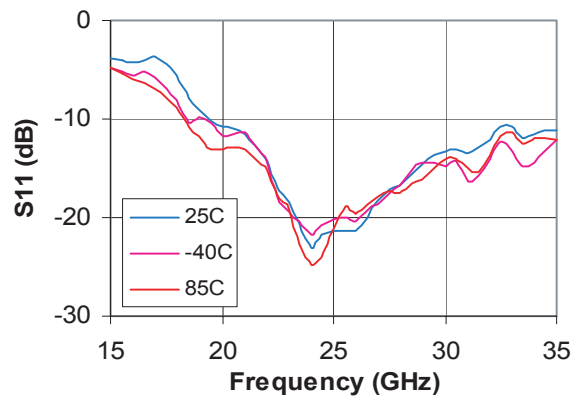


Figure 17. Output P-1dB Over Vdd

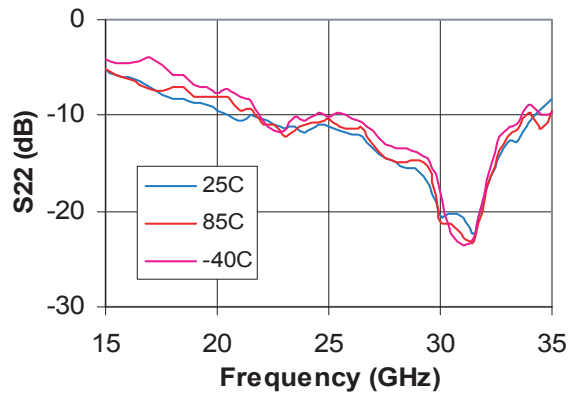


Figure 18. Output IP3 Over Vdd

AMMC-6232 Application and Usage

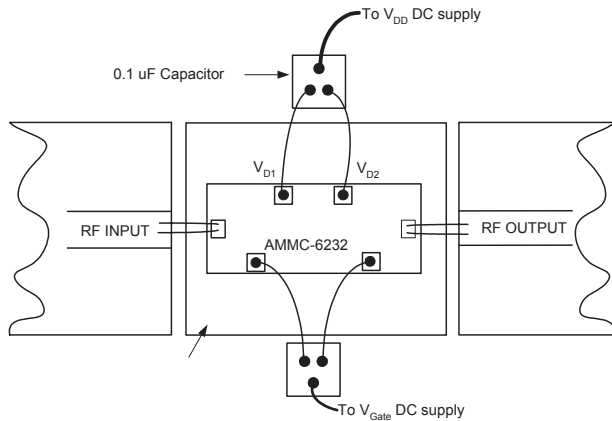


Figure 19. Gate Bias Combined Together

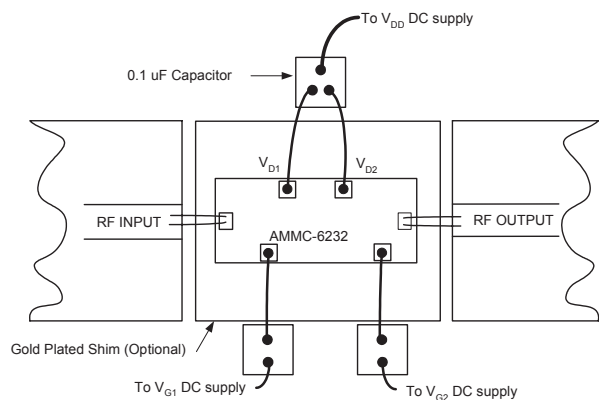


Figure 20. Separated Gate Bias

Biasing and Operation

The AMMC-6232 is normally biased with a positive drain supply connected to the VD1 and VD2 pads through bypass capacitor as shown in Figures 15 and 16. The recommended drain voltage and gate voltage for general usage is 4V and -0.95V respectively. With $V_{dd}=4V$, $V_g=-0.95V$, the corresponding drain current is approximately 135mA. It is important to have at least 0.1uF bypass capacitor and the capacitor should be placed as close to the component as possible. Aspects of the amplifier performance may be improved over a narrower bandwidth by application of additional conjugate, linearity, or low noise (T_{opt}) matching.

After adjusting the gate bias to obtain 135mA at $V_{dd} = 4V$, the AMMC-6232 can be safely biased at $V_{dd}=3V$ or $5V$ (while fixing the gate bias) as desired. At 4V, the performance is an optimal compromise between power consumption, gain and power/linearity. It is both applicable to be used as a low noise block or driver. At 3V, the amplifier is ideal as a front end low noise block where linearity is not highly required. At 5V, the amplifier can provide ~ 2dB more output power for LO or transmitter driver applications where high output power and linearity are often required.

The two gate voltages can be combined as shown in Figure 15 or separated as in Figure 16. Combining the two gate voltages simplifies the usage whereas separating them provides flexibility to overall biasing scheme.

In both cases, bonding wires at the input and output in the range of 0.15nH would likely improve the overall Noise Figure and input, output match at most frequencies.

No ground wires are needed because ground connection is made with plated through-holes to the backside of the substrate.

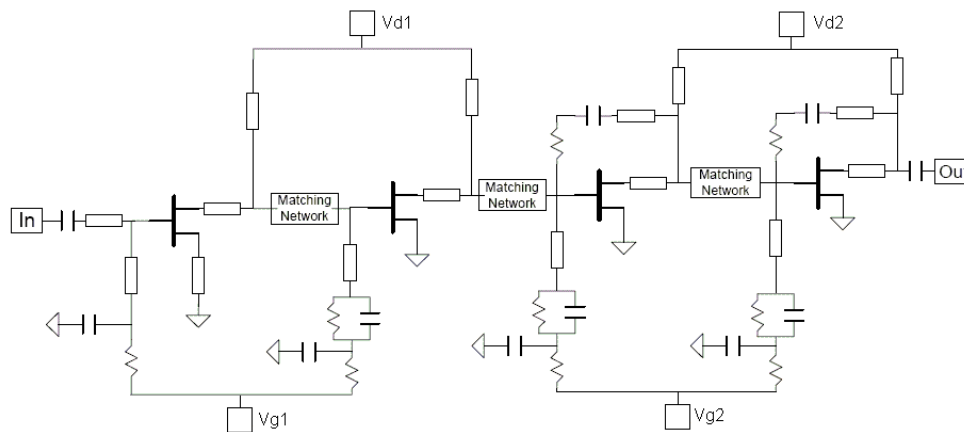


Figure 21. Simplified High Linearity LNA Schematic

Assembly Techniques

The backside of the MMIC chip is RF ground. For microstrip applications the chip should be attached directly to the ground plane (e.g. circuit carrier or heatsink) using electrically conductive epoxy [1,2].

For best performance, the topside of the MMIC should be brought up to the same height as the circuit surrounding it. This can be accomplished by mounting a gold plated metal shim (same length as the MMIC) under the chip which is of correct thickness to make the chip and adjacent circuit the same height. The amount of epoxy used for the chip or shim attachment should be just enough to provide a thin fillet around the bottom perimeter of the chip. The ground plane should be free of any residue that may jeopardize electrical or mechanical attachment.

RF connections should be kept as short as reasonable to minimize performance degradation due to undesirable series inductance. A single bond wire is normally sufficient for signal connections, however double bonding with 0.7mil gold wire will reduce series inductance. Gold thermo-sonic wedge bonding is the preferred method for wire attachment to the bond pads. The recommended wire bond stage temperature is $150^{\circ}\text{C} \pm 2^{\circ}\text{C}$.

Caution should be taken to not exceed the Absolute Maximum Rating for assembly temperature and time.

The chip is 100um thick and should be handled with care. This MMIC has exposed air bridges on the top surface and should be handled by the edges or with a custom collet (do not pick up the die with a vacuum on die center). Bonding pads and chip backside metallization are gold.

This MMIC is also static sensitive and ESD precautions should be taken

Notes:

1. Ablebond 84-1 LMI silver epoxy is recommended.
2. Eutectic attach is not recommended and may jeopardize reliability of the device.

Ordering Information:

AMMC-6232-W10 = 10 devices per tray

AMMC-6232-W50 = 50 devices per tray

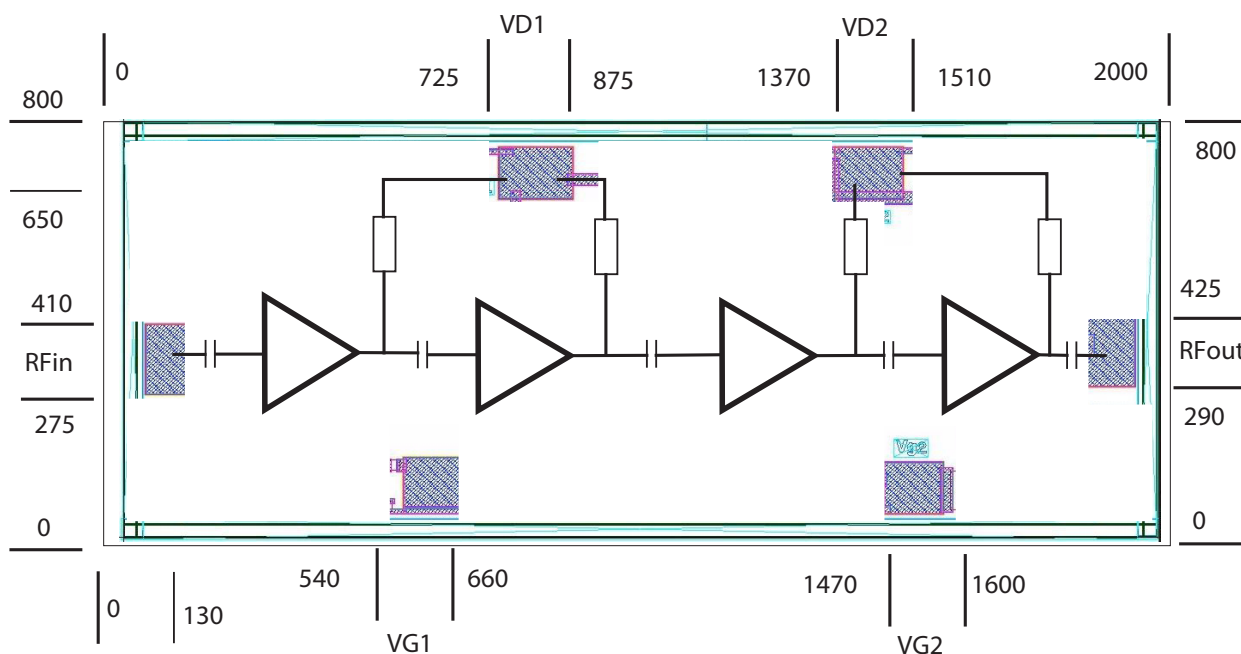


Figure 22. Bond Pad Locations

For product information and a complete list of distributors, please go to our web site: www.avagotech.com

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